

March 2013

# FQPF47P06 / FQPF47P06YDTU P-Channel QFET® MOSFET

-60 V, -30 A, 26 m $\Omega$ 

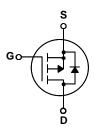
#### **Description**

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor® s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### **Features**

- -30 A, -60 V,  $R_{DS(on)}$ =26 m $\Omega(Max.)$  @ $V_{GS}$ =-10 V,  $I_D$ =-15 A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (Typ. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		FQPF47P06 / FQPF47P06YDTU	Unit
V <sub>DSS</sub>	Drain-Source Voltage		-60	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ ) - Continuous ( $T_C = 100^{\circ}C$ )		-30	Α
			-21.2	Α
$I_{DM}$	Drain Current - Pulsed	(Note 1)	-120	Α
$V_{GSS}$	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	820	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-30	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	6.2	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C		62	W
			0.41	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C
'L			300	

## **Thermal Characteristics**

Symbol	Parameter	Тур	Max	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		2.42	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-60			V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = -250 μA, Referenced to 25°C		-0.06		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-1	μΑ
		V <sub>DS</sub> = -48 V, T <sub>C</sub> = 150°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -15 A		0.021	0.026	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -30 V, I <sub>D</sub> = -15 A (Note 4)		19		S
C <sub>oss</sub>	Output Capacitance Reverse Transfer Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0  MHz		1300 320	1700 420	pF pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1.0 MHz		320	420	рF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -30 V, I <sub>D</sub> = -23.5 A,		50	110	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = -30 \text{ V}, I_D = -23.3 \text{ A},$ $R_G = 25 \Omega$		450	910	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	11.6 - 20 32		100	210	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4, 5)		195	400	ns
Qg	Total Gate Charge	V <sub>DS</sub> = -48 V, I <sub>D</sub> = -47 A,		84	110	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V		18		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4, 5)		44		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-30	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	Forward Current			-120	Α
	D : 0 D: 1 E 11/1/	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -30 A			-4.0	V
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	VGS - 0 V, IS - 00 /			7.0	
V <sub>SD</sub> t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_S = -47 \text{ A},$		130		ns

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 1.06mH, I<sub>AS</sub> = -30A, V<sub>DD</sub> = -25V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C 3. I<sub>SD</sub>  $\leq$  -47A, di/dt  $\leq$  300A/μs, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C 4. Pulse Test : Pulse width  $\leq$  300μs, Duty cycle  $\leq$  2% 5. Essentially independent of operating temperature

# **Typical Characteristics**

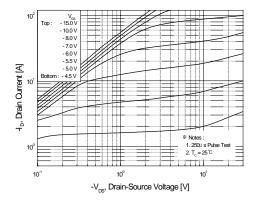


Figure 1. On-Region Characteristics

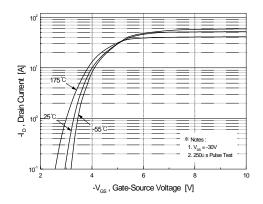


Figure 2. Transfer Characteristics

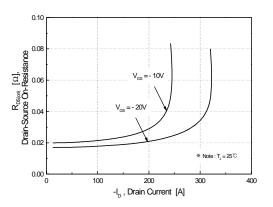


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

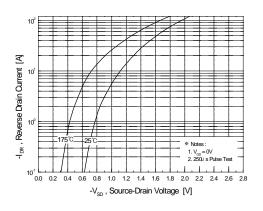


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

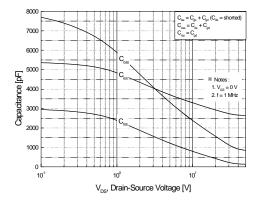


Figure 5. Capacitance Characteristics

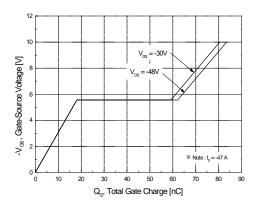
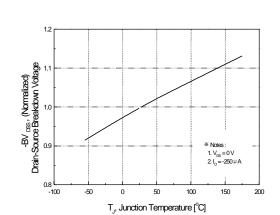


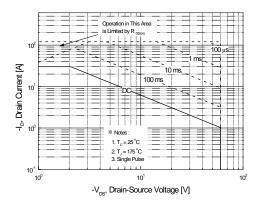
Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



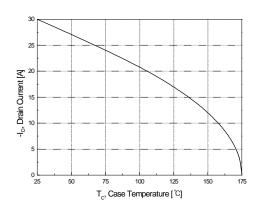


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

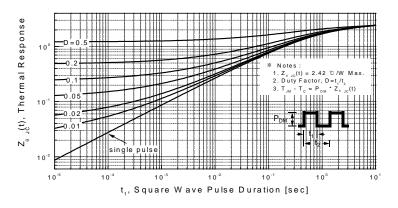
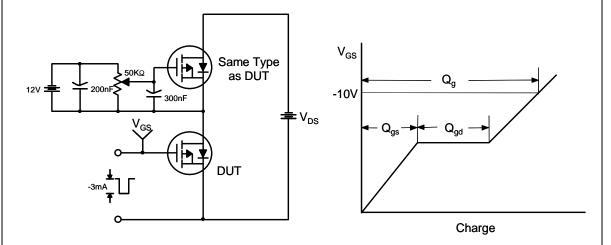
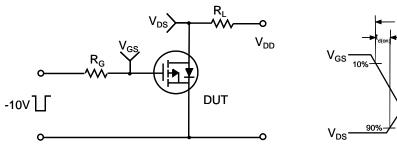


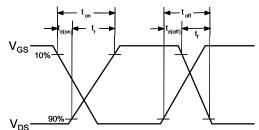
Figure 11. Transient Thermal Response Curve

#### **Gate Charge Test Circuit & Waveform**

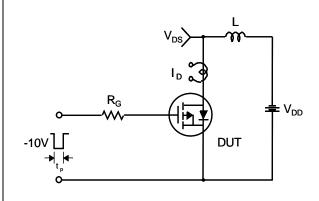


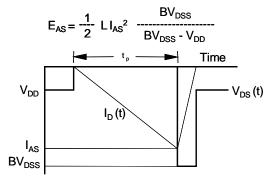
### **Resistive Switching Test Circuit & Waveforms**



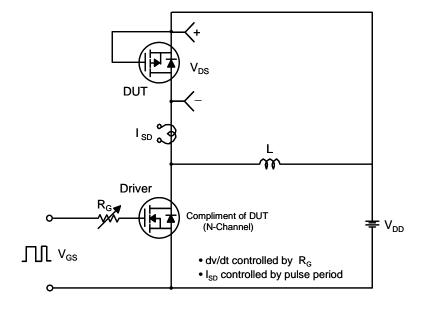


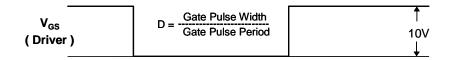
### **Unclamped Inductive Switching Test Circuit & Waveforms**

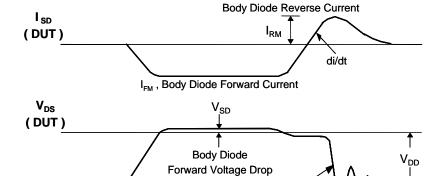




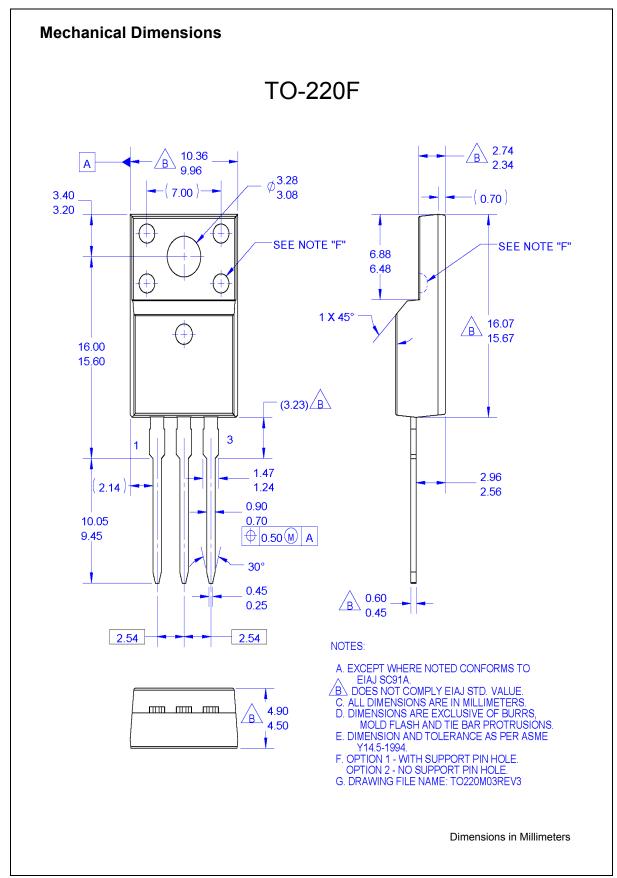
#### Peak Diode Recovery dv/dt Test Circuit & Waveforms

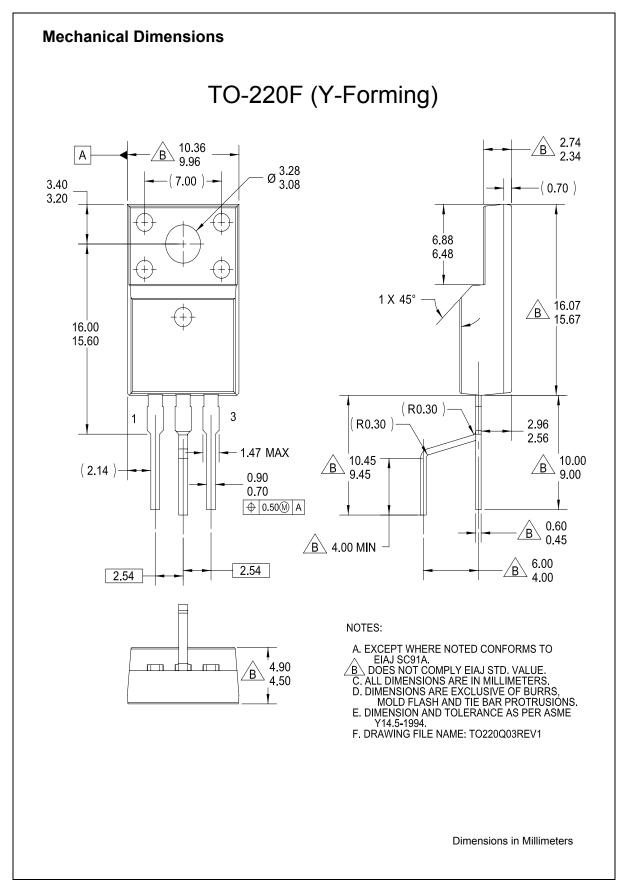






Body Diode Recovery dv/dt









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